



Spin blockade lifting due to phonon mediated spin relaxation and electric dipole spin resonance in nanowire quantum dots

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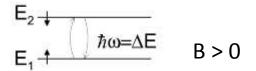




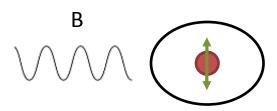


Electrical control over a single spin

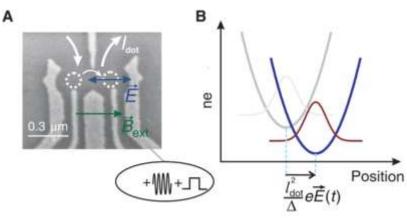
- quantum computation on spin qubits
- spins in quantum dots quantum gates
- single gates require spin rotations



Rabi oscillation in AC magnetic field – low scalability



spin-orbit interaction, spin oscillations in an effective magnetic field



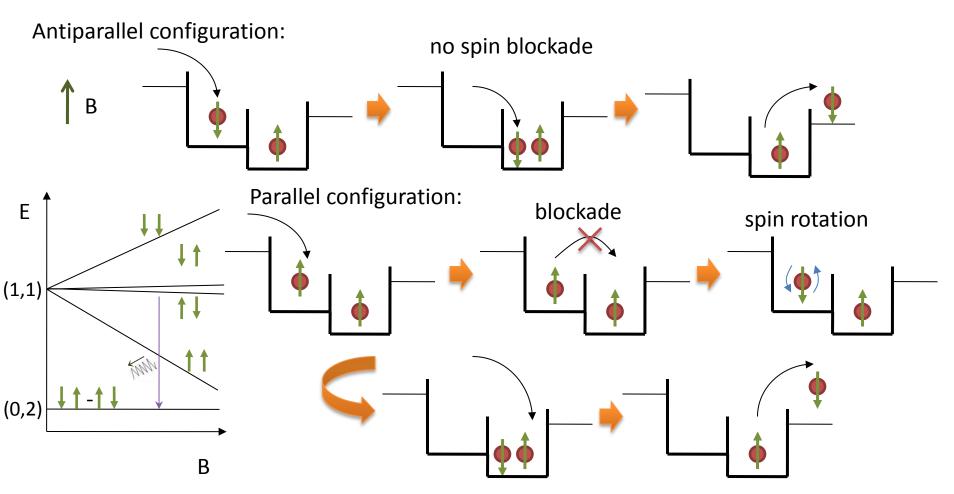
K. C. Nowack, et al., Science 318, 1430 (2007).

$$\hat{H}_{SO} = \frac{\hbar \nabla V}{4m_0^2 c^2} \cdot (\boldsymbol{\sigma} \times \mathbf{p})$$

Electric Dipole Spin Resonance (EDSR)

Spin to charge conversion

Spin blockade in double dots allows for the measurement of the spin state



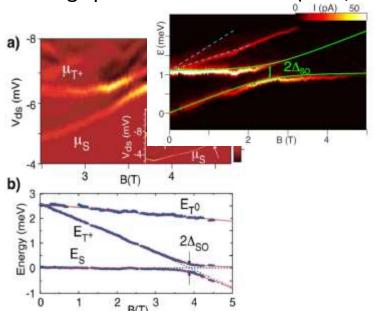
Energy dissipated by phonons

Sequential events - current increases when the spin is rotated At the resonances

Nanowire quantum dots

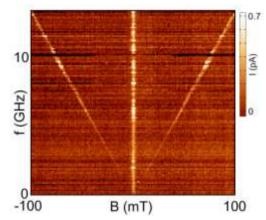
Measured map of the current due to spin blockade lifting.

Strong spin-orbit interaction (InSb, InAs)



C. Fasth et al., Phys. Rev. Lett., **98**, 266801 (2007) A. Pfund et al., Phys. Rev. B **76**, 161308(R) (2007)



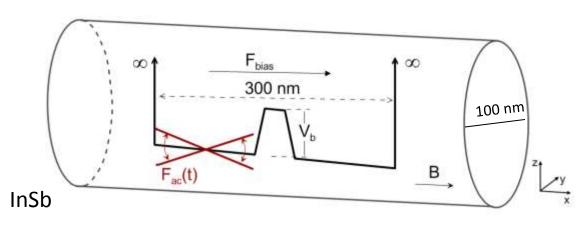


S. Nadj-Perge, et al., Nature (London) 468, 1084 (2010).

Strong SOI -> spin relaxation

How does this affects EDSR observed due to spin blockade lifting?

Theory – model system



$$H_{1D}(t) = h_{1D}^1(t) + h_{1D}^2(t) + \frac{\sqrt{\pi/2}}{4\pi\varepsilon_0\varepsilon l} \operatorname{erfcx}\left[\frac{|x_1 - x_2|}{\sqrt{2}l}\right]$$

$$h_{1D}(t) = \frac{\hbar^2 k_x^2}{2m^*} + V(x, t) - \alpha \sigma_y k_x + \frac{1}{2} \mu_B g(x) B \sigma_x$$

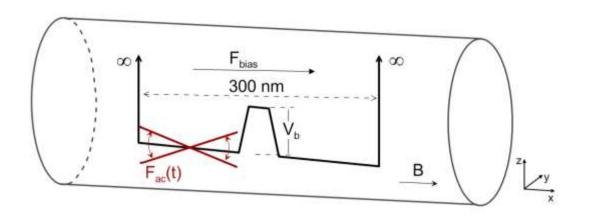
- Coupled QDs in a nanowire
- Quasi one-dimensional
- Two electrons
- Electric field present in one of the dots
- Magnetic field along the structure
- Different g-factors in the dots
- Bias voltage

$$\tau_{if}^{-1} = \frac{2\pi}{\hbar} \sum_{\nu,i=1,2} \int_{\mathbf{q}} dq |M_{\nu}(\mathbf{q})|^2 \times |\langle \Psi^f | e^{-i\mathbf{q}\mathbf{r_i}} |\Psi^i \rangle|^2 \delta(|E^f - E^i| - E_q)$$

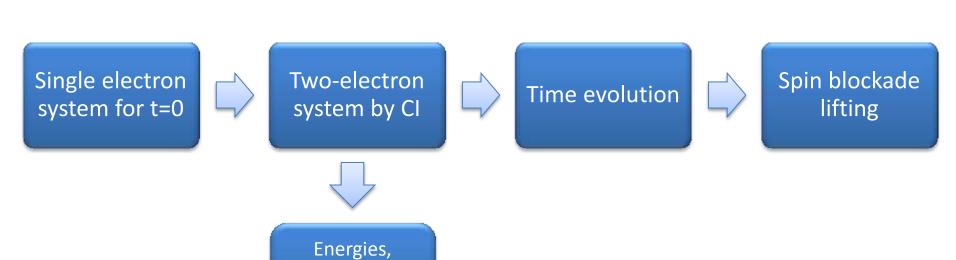
$$E_q = \hbar c_{\nu} |\mathbf{q}|$$

Electron
scattering on
piezoelectric and
deformation
potentials

Theory – model system



relaxation times



Relaxation time

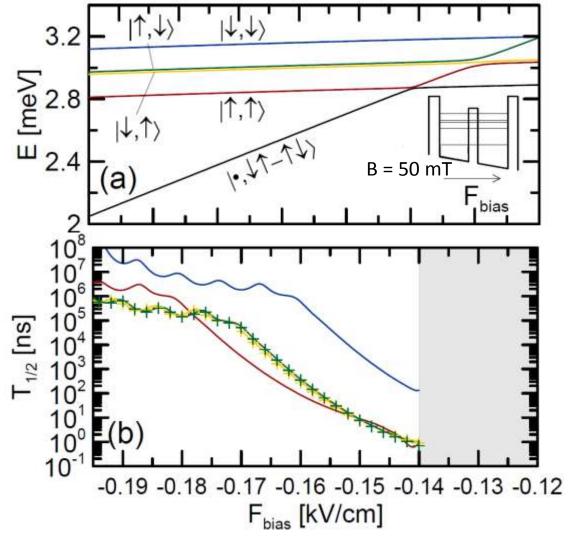
How relaxation times change as function of F_{bias} ?

Half life due to relaxation to the groundstate:

$$T_{1/2} = \ln(2)/\tau_{if}$$

 $|\uparrow,\uparrow\rangle$ relaxes in nanosecond, $|\downarrow,\downarrow\rangle$ relaxes in microseconds

Without oscillating electric field, $F_{AC} = 0$

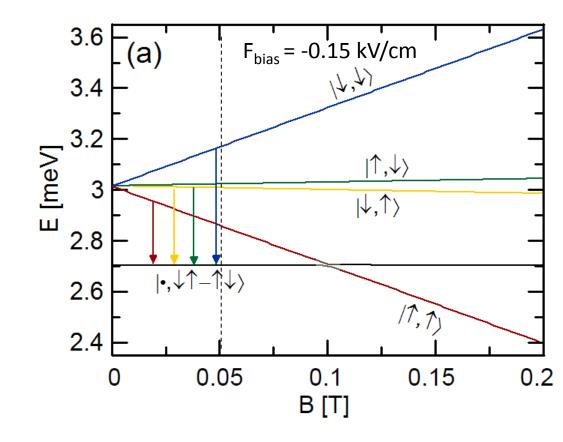


Relaxation time

Zeeman splitting

B < 100 mT relaxation time of spin positive triplet comparable to S = 0 states

B = 100 mT singlet triplet anticrossing

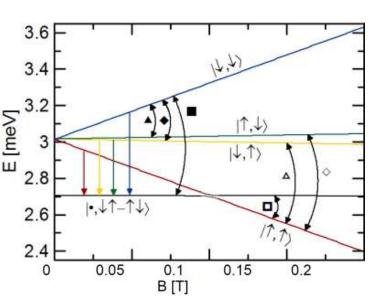


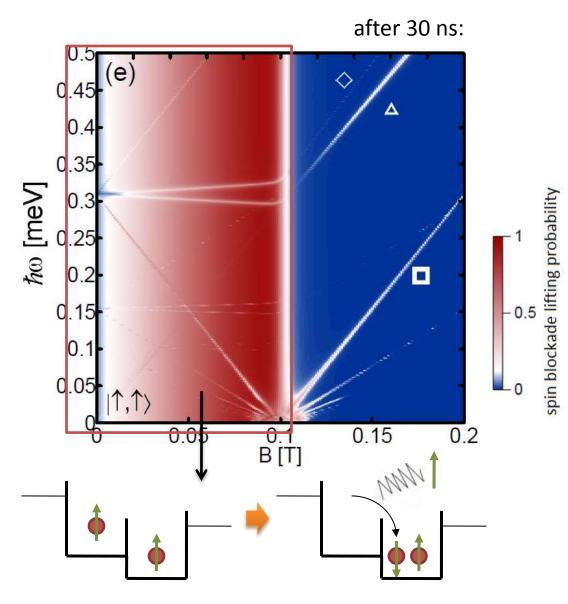
B > 100 mT spin positive triplet blocked again



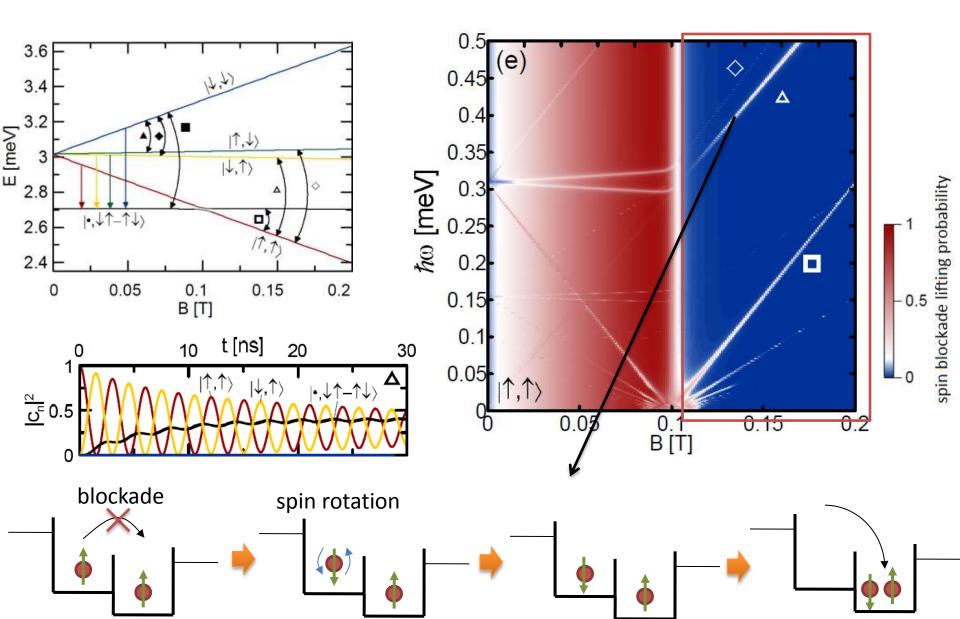
Nonzero driving field F_{AC}

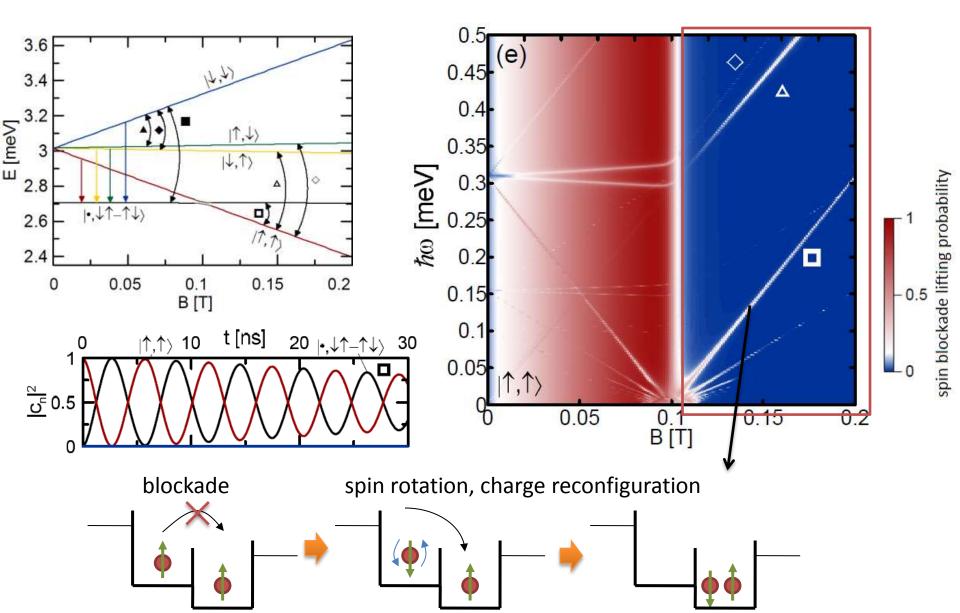
 $|\uparrow,\uparrow\rangle$ As an initial condition

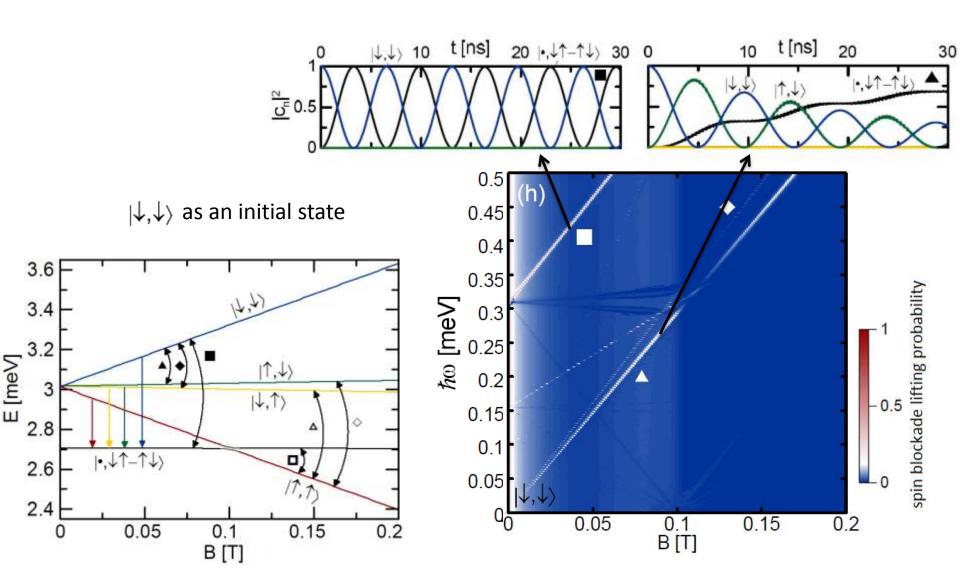




No blockade, no EDSR observed



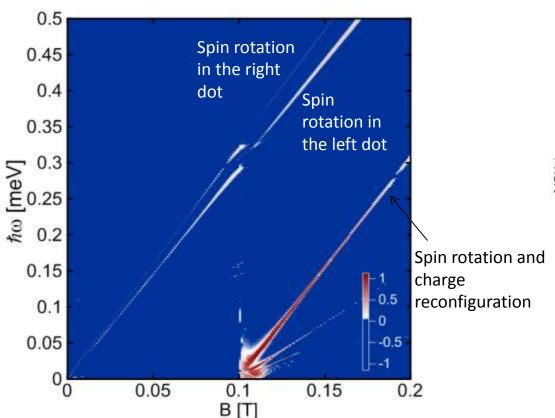




Comparison with the experiment

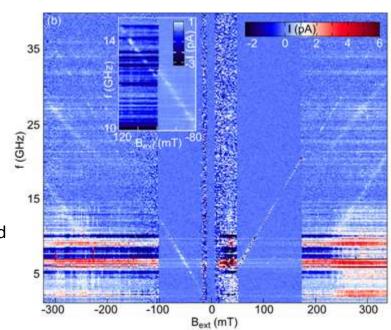
In real system all the 4 states are initialized

Total probability of spin blockade lifting with removed background for $F_{AC} = 0$.



M.P. Nowak, B. Szafran arXiv: 1303.0211 (2013)

Similar set of lines observed in the experimental maps of the current:



S. M. Frolov, et al., Phys. Rev. Lett. **109**, 236805 (2012).

Conclusions

- In a nanowire QDs the relaxation rate governed mainly by the energy difference not the spin polarization
- Strong spin-orbit interaction results in deblocking the spin positive triplet before the anticrossing
- EDSR can produce two kind of resonance lines
 - Direct transitions with charge reconfiguration (1,1) -> (0,2) observed after singlet-triplet acticrossing
 - Indirect transitions with the (1,1) -> (0,2) transition mediated by phonons.

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